

APPENDIX:

The Appendix includes the following item(s):

- ☒ - a new or amended Abstract of the Disclosure

ABSTRACT OF THE DISCLOSURE

An MRAM has a plurality of bit lines, a reference bit line, a plurality of memory cells and reference cells and a read section. The memory cells are provided along the bit lines and the reference cells along the reference bit line. The memory cell and reference cell have a tunneling magnetic resistance and a reference tunneling magnetic resistance, each of which has a spontaneous magnetization whose direction is reversed in accordance with data stored therein. The read section has a first resistance section which contains a ninth terminal connected with a bit line and a tenth terminal connected with the first power supply, a second resistance section which contains an eleventh terminal connected with the reference bit line and a twelfth terminal connected with the first power supply, and a comparing section which compares a sense voltage on the ninth terminal and a reference voltage of the eleventh terminal.